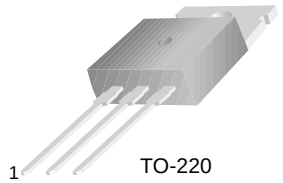
SYC SEMICONDUCTORES Y COMPONENTES

BU407/407H

High Voltage Switching

- Use In Horizontal Deflection Output Stage



TO-220

1.Base 2.Collector 3.Emitter

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	330	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current (DC)	7	A
I_{CP}	Collector Current (Pulse)	10	A
I_B	Base Current	4	A
P_C	Collector Dissipation (T_C=25°C)	60	W
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	- 65 ~ 150	°C

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
I_{CES}	Collector Cut-off Current	V_{CE} = 330V, V_{BE} = 0 V_{CE} = 200V, V_{BE} = 0 V_{CE} = 200V, V_{BE} = 0 @ T_C= 150°C		5 100 1	mA µA mA
I_{EBO}	Emitter Cut-off Current	V_{BE} = 6V, I_C = 0		1	mA
V_{CE}(sat)	Collector-Emitter Saturation Voltage : BU407 : BU407H	 I_C = 5A, I_B = 0.5A I_C = 5A, I_B = 0.8A		 1 1	 V V
V_{BE}(sat)	Base-Emitter Saturation Voltage : BU407 : BU407H	 I_C = 5A, I_B = 0.5A I_C = 5A, I_B = 0.8A		 1.2 1.2	 V V
f_T	Current Gain Bandwidth Product	V_{CE} = 10V, I_C = 0.5A	10		MHz
t_{OFF}	Turn OFF Time : BU407 : BU407H	 I_C = 5A, I_B = 0.5A I_C = 5A, I_B = 0.8A		 0.75 0.4	 µs µs

Typical Characteristics

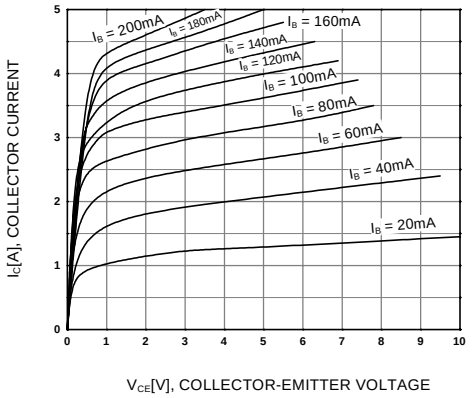


Figure 1. Static Characteristic

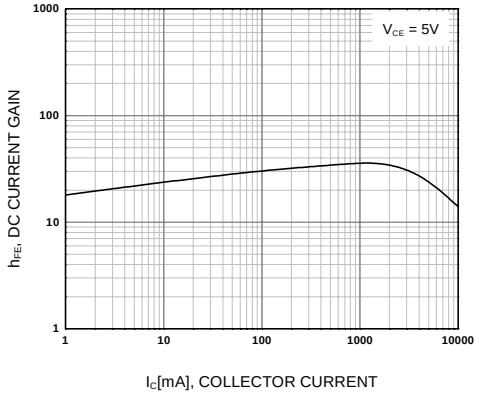


Figure 2. DC current Gain

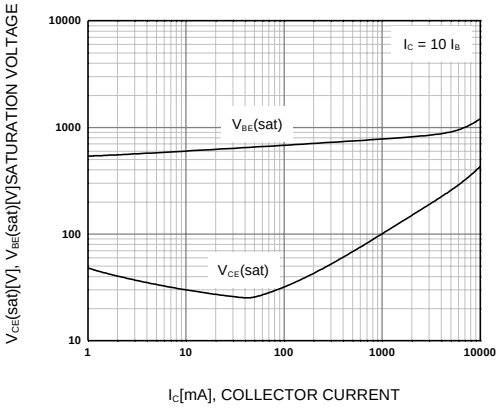


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

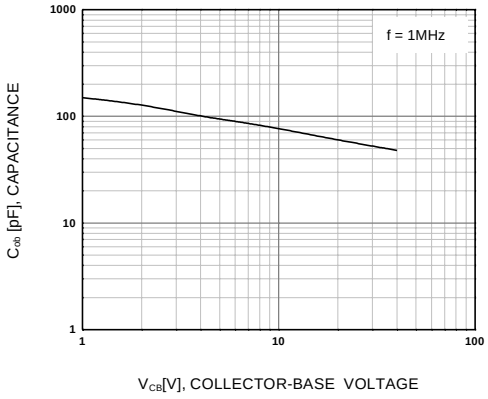


Figure 4. Collector Output Capacitance

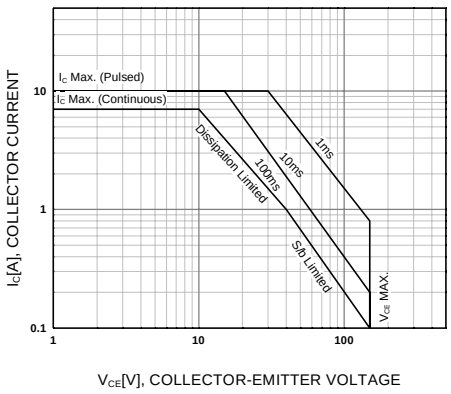


Figure 5. Safe Operating Area

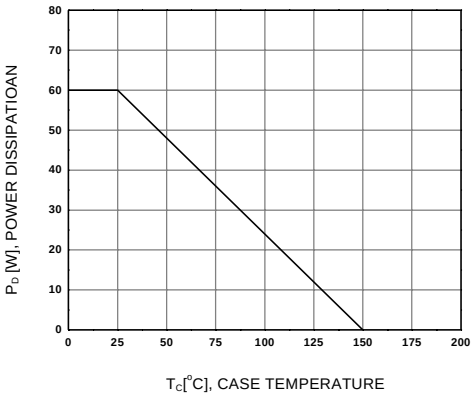
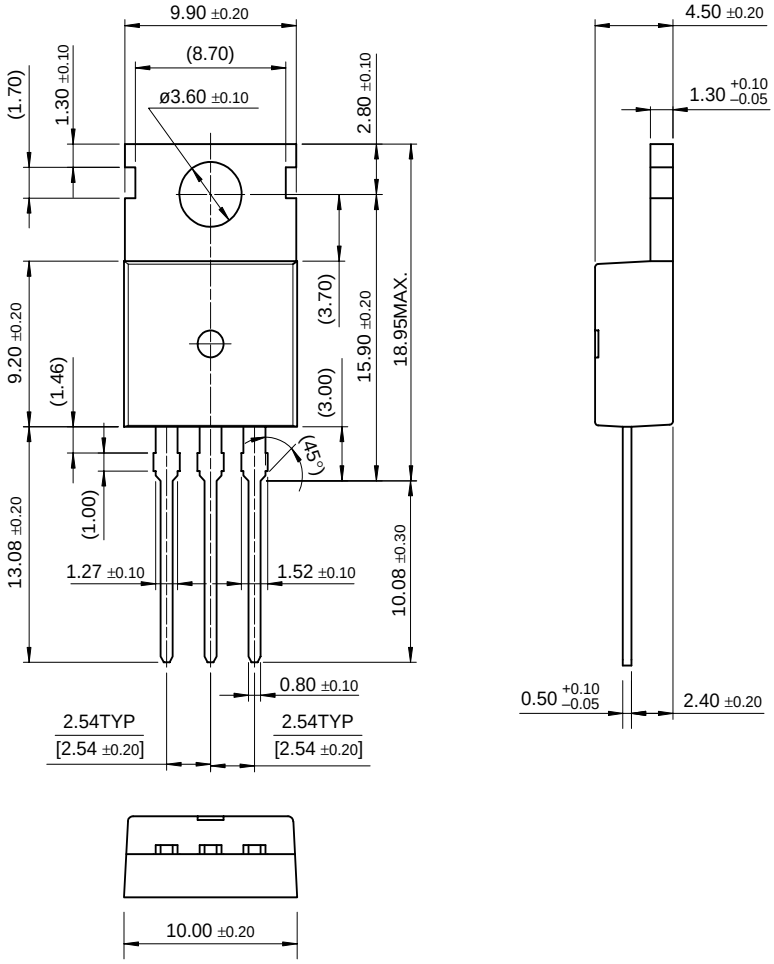


Figure 6. Power Derating

Package Demensions

TO-220



Dimensions in Millimeters